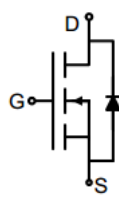
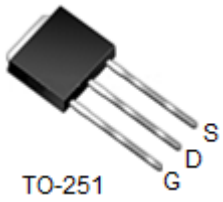


# N-Channel Enhancement Mode Power MOSFET

<p><b>Description</b></p> <p>The G20N06J uses advanced trench technology to provide excellent <math>R_{DS(ON)}</math>, low gate charge. It can be used in a wide variety of applications.</p> <p><b>General Features</b></p> <ul style="list-style-type: none"> <li>● <math>V_{DS}</math> 60V</li> <li>● <math>I_D</math> (at <math>V_{GS} = 10V</math>) 20A</li> <li>● <math>R_{DS(ON)}</math> (at <math>V_{GS} = 10V</math>) &lt; 23mΩ</li> <li>● 100% Avalanche Tested</li> <li>● RoHS Compliant</li> </ul> <p><b>Application</b></p> <ul style="list-style-type: none"> <li>● Power switch</li> <li>● DC/DC converters</li> </ul>		 <p>Schematic Diagram</p>  <p>TO-251</p>	
<b>Device</b>	<b>Package</b>	<b>Marking</b>	<b>Packaging</b>
G20N06J	TO-251	G20N06	70pcs/Tube

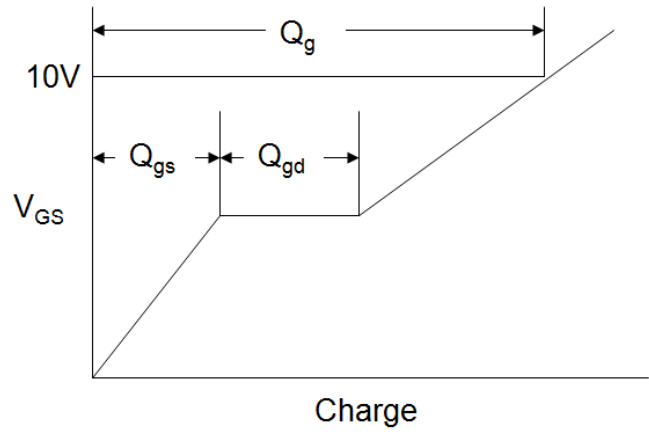
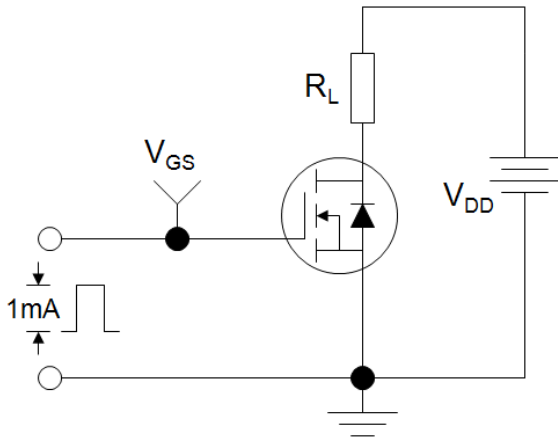
Absolute Maximum Ratings $T_C = 25^{\circ}C$ , unless otherwise noted			
Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	60	V
Continuous Drain Current	$I_D$	20	A
Pulsed Drain Current (note1)	$I_{DM}$	80	A
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Power Dissipation	$P_D$	38	W
Single pulse avalanche energy (note3)	$E_{AS}$	36	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 To 150	$^{\circ}C$
Thermal Resistance			
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{thJC}$	3.3	$^{\circ}C/W$

Specifications $T_J = 25^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
<b>Static Parameters</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	60	--	--	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 60V, V_{GS} = 0V$	--	--	1	$\mu A$
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 20V$	--	--	$\pm 100$	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1	1.5	2	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 20A$	--	20	27	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=5V, I_D=5A$	11	--	--	S
<b>Dynamic Parameters</b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0V,$ $V_{DS} = 30V,$ $f = 1.0MHz$	--	500	--	pF
Output Capacitance	$C_{oss}$		--	60	--	
Reverse Transfer Capacitance	$C_{rss}$		--	25	--	
Total Gate Charge	$Q_g$	$V_{DS} = 30V,$ $I_D = 4.5A,$ $V_{GS} = 10V$	--	25	--	nC
Gate-Source Charge	$Q_{gs}$		--	4.5	--	
Gate-Drain Charge	$Q_{gd}$		--	6.5	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 30V,$ $I_D = 2A,$ $R_G = 3\Omega$	--	5	--	ns
Turn-on Rise Time	$t_r$		--	2.6	--	
Turn-off Delay Time	$t_{d(off)}$		--	16.1	--	
Turn-off Fall Time	$t_f$		--	2.3	--	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Body Diode Current	$I_S$	$T_C = 25^\circ\text{C}$	--	--	20	A
Body Diode Voltage	$V_{SD}$	$T_J = 25^\circ\text{C}, I_{SD} = 10A, V_{GS} = 0V$	--	--	1.2	V

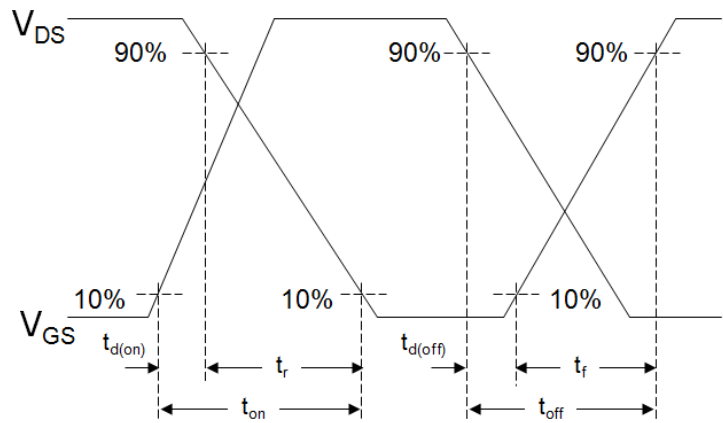
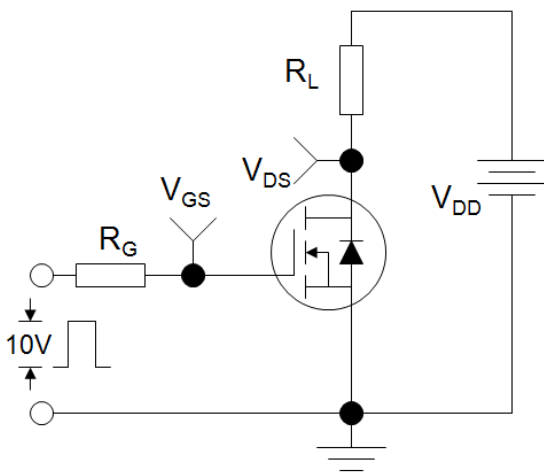
**Notes**

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. Identical low side and high side switch with identical  $R_G$
3. EAS condition :  $T_J=25^\circ\text{C}$  ,  $V_{DD}=50V, V_{GS}=10V, L=0.5mH, R_g=25\Omega$

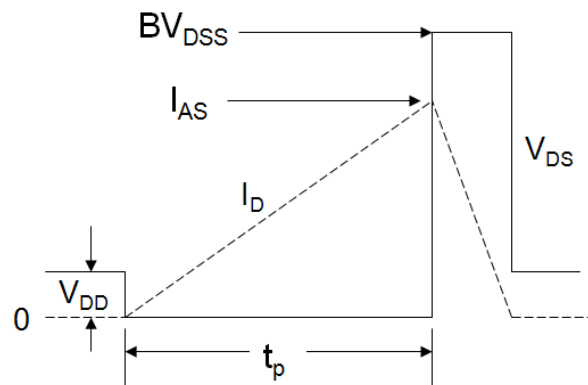
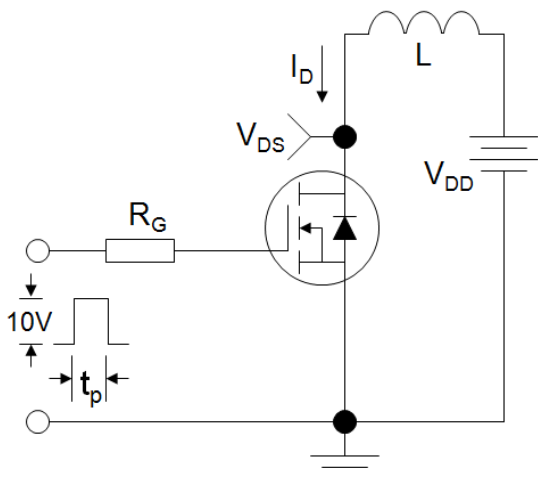
Gate Charge Test Circuit



EAS Test Circuit



Switch Time Test Circuit



Typical Characteristics  $T_J = 25^\circ\text{C}$ , unless otherwise noted

Figure 1. Output Characteristics

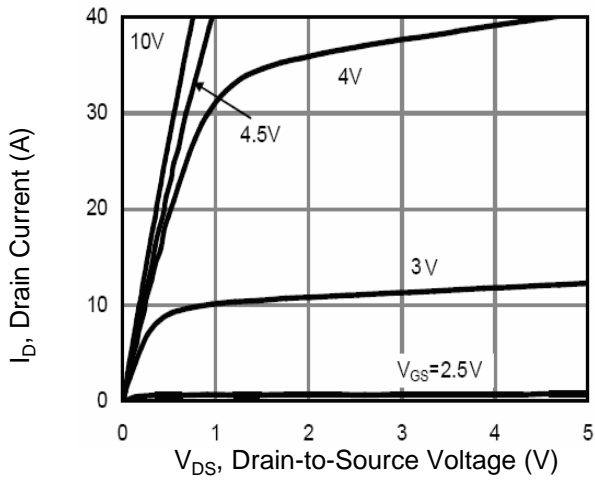


Figure 2. Transfer Characteristics

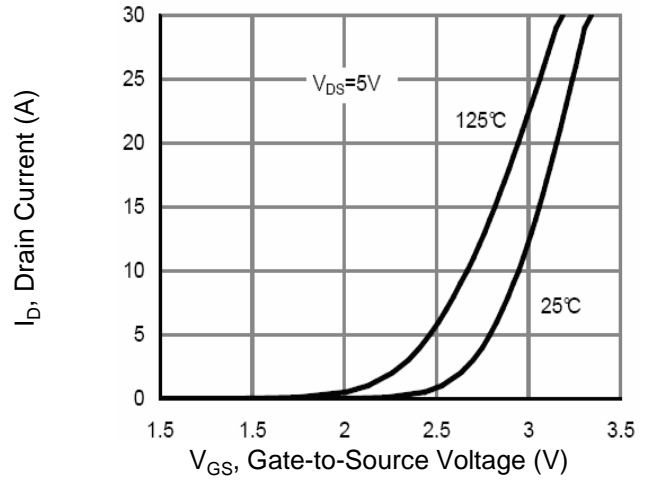


Figure 3. Gate Charge

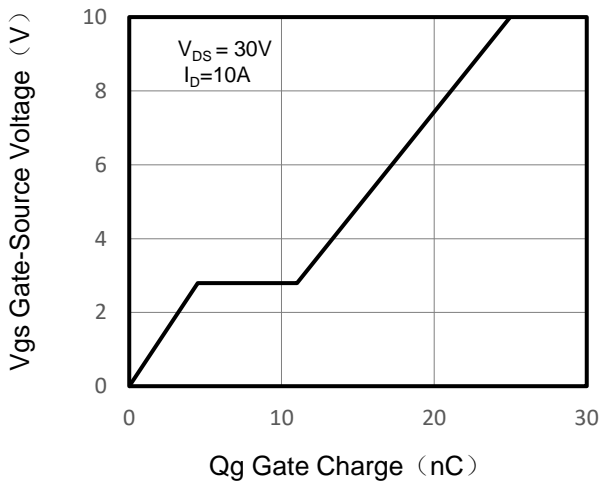


Figure 4. Drain Source On Resistance

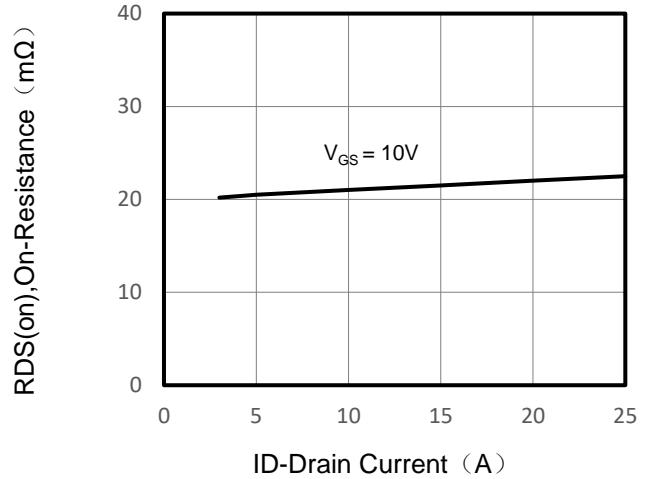


Figure 5. Capacitance vs Vds

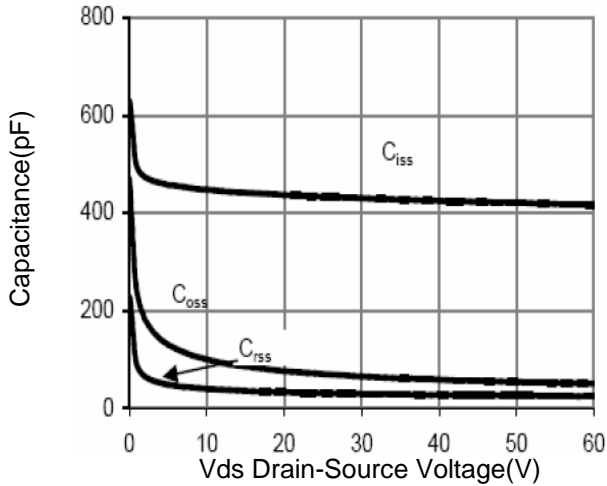
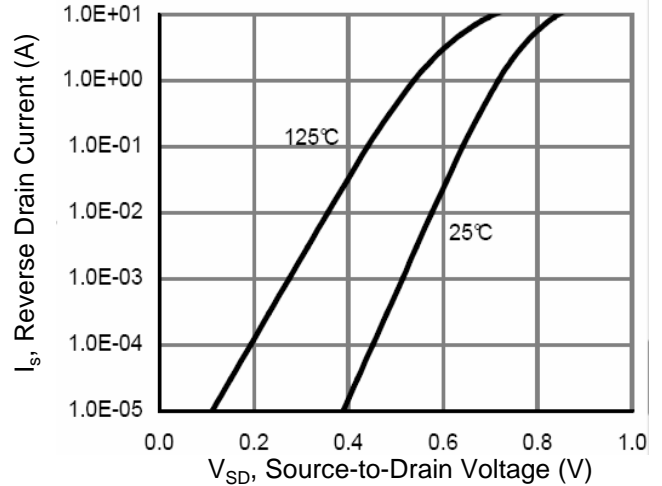


Figure 6. Source-Drain Diode Forward



Typical Characteristics  $T_J = 25^\circ\text{C}$ , unless otherwise noted

Figure 7. Drain-Source On-Resistance

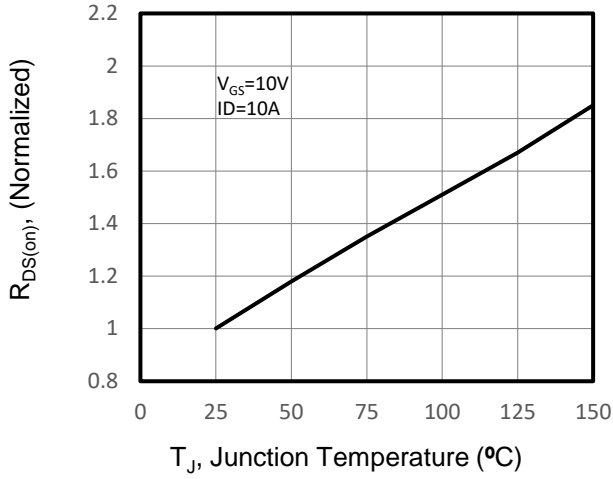


Figure 8. Safe Operation Area

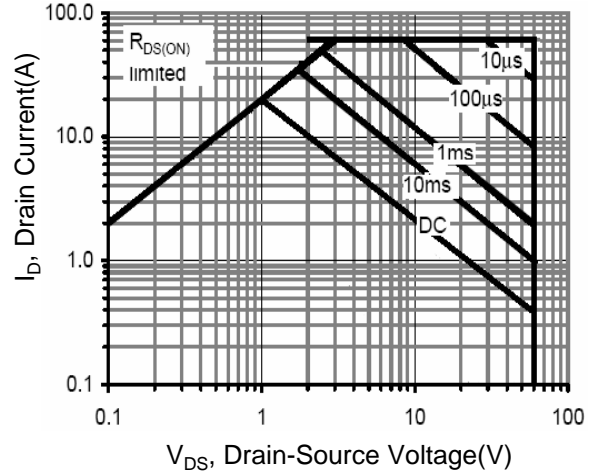
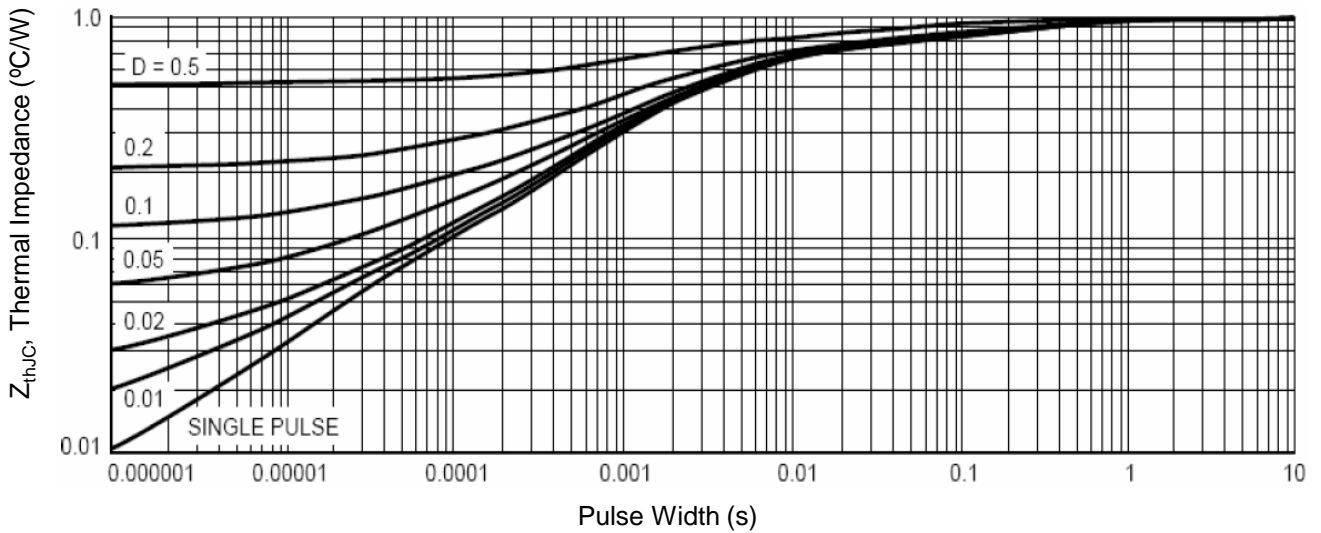
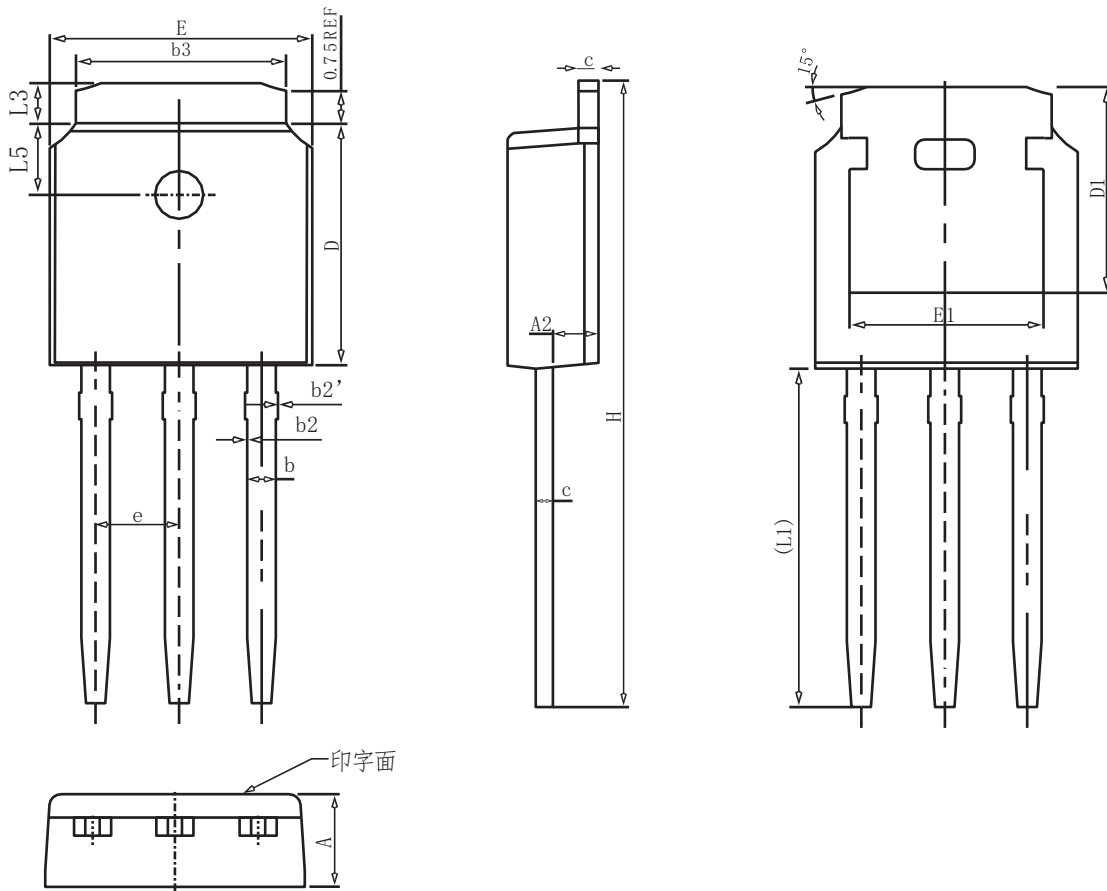


Figure 9. Normalized Maximum Transient Thermal Impedance



TO-251 Package information



COMMON DIMENSIONS

SYMBOL	mm		
	MIN	NOM	MAX
A	2.20	2.30	2.40
A2	0.97	1.07	1.17
b	0.68	0.78	0.90
b2	0.00	0.04	0.10
b2'	0.00	0.04	0.10
b3	5.20	5.33	5.50
c	0.43	0.53	0.63
D	5.98	6.10	6.22
D1	5.30REF		
E	6.40	6.60	6.80
E1	4.63	-	-
e	2.286BSC		
H	16.22	16.52	16.82
L1	9.15	9.40	9.65
L3	0.88	1.02	1.28
L5	1.65	1.80	1.95